PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

MPSA94

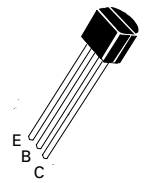
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FEATURES

* High voltage

APPLICATIONS

* Telephone dialler circuit



TO92

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	I_C	-300	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	625	mW
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-400			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-400			V	I_C=-1mA, I_B=0*
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	-400			V	IC=-100μA, I_E=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6			V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}			-0.1	μA	V_{CB}=-400V, I_E=0
Collector Cut-Off Current	I_{CES}			-500	nA	VCE=-400V
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	V_{EB}=-4V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.4 -0.5 -0.75	V	I_C=-1mA, I_B=-0.1mA* I_C=-10mA, I_B=-1mA* I_C=-50mA, I_B=-5mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.75	V	I_C=-10mA, I_B=-1mA*
Static Forward Current Transfer Ratio	h_{FE}	40 50 45 40		300		I_C=-1mA, V_{CE}=-10V* I_C=-10mA, V_{CE}=-10V* I_C=-50mA, V_{CE}=-10V* I_C=-100mA, V_{CE}=-10V*

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%